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# FSQ0365, FSQ0265, FSQ0165, FSQ321 Green Mode Fairchild Power Switch (FPS™) for Valley Switching Converter – *Low EMI and High Efficiency*

## Features

- Optimized for Valley Switching Converter (VSC)
- Low EMI through Variable Frequency Control and Inherent Frequency Modulation
- High Efficiency through Minimum Voltage Switching
- Narrow Frequency Variation Range Over Wide Load and Input Voltage Variation
- Advanced Burst-Mode Operation for Low Standby Power Consumption
- Pulse-by-Pulse Current Limit
- Protection Functions: Overload Protection (OLP), Over-Voltage Protection (OVP), Abnormal Over-Current Protection (AOCP), Internal Thermal Shutdown (TSD)
- Under-Voltage Lockout (UVLO) with Hysteresis
- Internal Startup Circuit
- Internal High-Voltage SenseFET: 650V
- Built-in Soft-Start: 15ms

## Applications

- Power Supplies for DVP Player, DVD Recorder, Set-Top Box
- Adapter
- Auxiliary Power Supply for PC, LCD TV, and PDP TV

## Description

A Valley Switching Converter generally shows lower EMI and higher power conversion efficiency than a conventional hard-switched converter with a fixed switching frequency. The FSQ-series is an integrated Pulse-Width Modulation (PWM) controller and SenseFET specifically designed for valley switching operation with minimal external components. The PWM controller includes an integrated fixed-frequency oscillator, under-voltage lockout, Leading-Edge Blanking (LEB), optimized gate driver, internal soft-start, temperature-compensated precise current sources for loop compensation, and self-protection circuitry.

Compared with discrete MOSFET and PWM controller solutions, the FSQ-series reduces total cost, component count, size and weight; while simultaneously increasing efficiency, productivity, and system reliability. This device provides a basic platform for cost-effective designs of valley switching fly-back converters.

## Related Application Notes

- [AN-4137 - Design Guidelines for Offline Flyback Converters Using Fairchild Power Switch \(FPS™\)](#)
- [AN-4141 - Troubleshooting and Design Tips for Fairchild Power Switch \(FPS™\) Flyback Applications](#)
- [AN-4147 - Design Guidelines for RCD Snubber of Flyback Converters](#)
- [AN-4150 - Design Guidelines for Flyback Converters Using FSQ-series Fairchild Power Switch \(FPS™\)](#)
- [AN-4134 - Design Guidelines for Off-line Forward Converters Using Fairchild Power Switch \(FPS™\)](#)

## Ordering Information

Part Number	Package	Operating Temperature	Current Limit	R <sub>DS(ON)</sub> (Max.)	Maximum Output Table <sup>(1)</sup>				Replaces Devices
					230V <sub>AC</sub> ±15% <sup>(2)</sup>		85-265V <sub>AC</sub>		
					Adapter <sup>(3)</sup>	Open Frame <sup>(4)</sup>	Adapter <sup>(3)</sup>	Open Frame <sup>(4)</sup>	
FSQ321	8-DIP	-40 to +85°C	0.6A	19Ω	8W	12W	7W	10W	FSDL321 FSDM311
FSQ321L	8-LSOP								
FSQ321LX	8-LSOP (Tape & Reel)								
FSQ0165RN	8-DIP	-40 to +85°C	0.9A	10Ω	10W	15W	9W	13W	FSDL0165RN
FSQ0165RL	8-LSOP								
FSQ0165RLX	8-LSOP (Tape & Reel)								
FSQ0265RN	8-DIP	-40 to +85°C	1.2A	6Ω	14W	20W	11W	16W	FSDM0265RN FSDM0265RNB
FSQ0265RL	8-LSOP								
FSQ0365RN	8-DIP	-40 to +85°C	1.5A	4.5Ω	17.5W	25W	13W	19W	FSDM0365RN FSDM0365RNB
FSQ0365RL	8-LSOP								

### Notes:

1. The junction temperature can limit the maximum output power.
2. 230V<sub>AC</sub> or 100/115V<sub>AC</sub> with voltage doubler. The maximum power with CCM operation
3. Typical continuous power in a non-ventilated, enclosed adapter measured at 50°C ambient temperature.
4. Maximum practical continuous power in an open-frame design at 50°C ambient temperature.

### Application Circuit

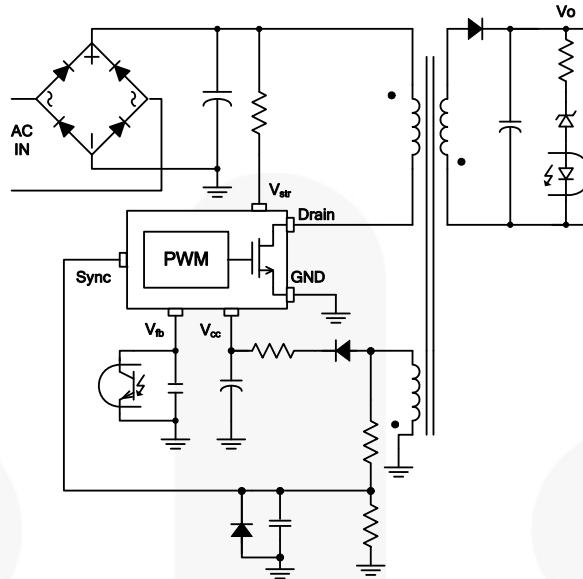


Figure 1. Typical Flyback Application

### Internal Block Diagram

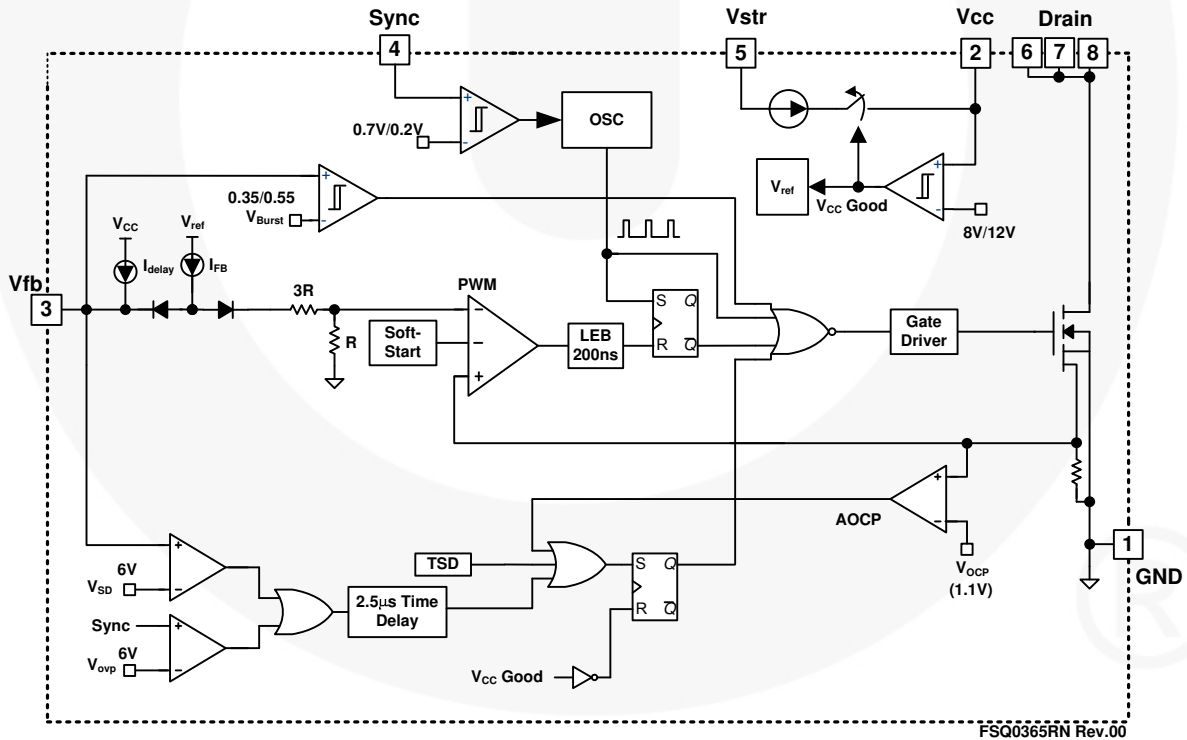
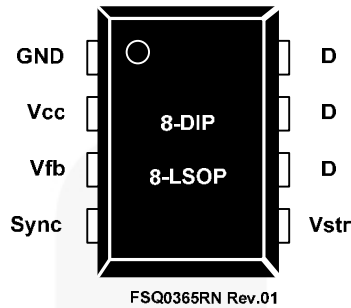


Figure 2. Internal Block Diagram

F5Q0365RN Rev.00

## Pin Assignments



**Figure 3. Pin Configuration (Top View)**

## Pin Definitions

Pin#	Name	Description
1	GND	SenseFET source terminal on primary side and internal control ground.
2	V <sub>CC</sub>	Positive supply voltage input. Although connected to an auxiliary transformer winding, current is supplied from pin 5 (V <sub>str</sub> ) via an internal switch during startup (see Figure 2). It is not until V <sub>CC</sub> reaches the UVLO upper threshold (12V) that the internal startup switch opens and device power is supplied via the auxiliary transformer winding.
3	V <sub>fb</sub>	The feedback voltage pin is the non-inverting input to the PWM comparator. It has a 0.9mA current source connected internally while a capacitor and opto-coupler are typically connected externally. There is a time delay while charging external capacitor C <sub>fb</sub> from 3V to 6V using an internal 5μA current source. This delay prevents false triggering under transient conditions, but still allows the protection mechanism to operate under true overload conditions.
4	Sync	This pin is internally connected to the sync-detect comparator for valley switching. Typically the voltage of the auxiliary winding is used as Sync input voltage and external resistors and capacitor are needed to make delay to match valley point. The threshold of the internal sync comparator is 0.7V/0.2V.
5	V <sub>str</sub>	This pin is connected to the rectified AC line voltage source. At startup, the internal switch supplies internal bias and charges an external storage capacitor placed between the V <sub>CC</sub> pin and ground. Once the V <sub>CC</sub> reaches 12V, the internal switch is opened.
6, 7, 8	Drain	The drain pins are designed to connect directly to the primary lead of the transformer and are capable of switching a maximum of 650V. Minimizing the length of the trace connecting these pins to the transformer decreases leakage inductance.

## Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.  $T_A=25^{\circ}\text{C}$ , unless otherwise specified.

Symbol	Parameter	Min.	Max.	Unit
$V_{STR}$	Vstr Pin Voltage	500		V
$V_{DS}$	Drain Pin Voltage	650		V
$V_{CC}$	Supply Voltage		20	V
$V_{FB}$	Feedback Voltage Range	-0.3	9.0	V
$V_{Sync}$	Sync Pin Voltage	-0.3	9.0	V
$I_{DM}$	Drain Current Pulsed <sup>(6)</sup>	FSQ0365	12.0	A
		FSQ0265	8.0	
		FSQ0165	4.0	
		FSQ321	1.5	
$E_{AS}$	Single Pulsed Avalanche Energy <sup>(7)</sup>	FSQ0365	230	mJ
		FSQ0265	140	
		FSQ0165	50	
		FSQ321	10	
$P_D$	Total Power Dissipation		1.5	W
$T_J$	Recommended Operating Junction Temperature	-40	Internally Limited	$^{\circ}\text{C}$
$T_A$	Operating Ambient Temperature	-40	+85	$^{\circ}\text{C}$
$T_{STG}$	Storage Temperature	-55	+150	$^{\circ}\text{C}$
ESD	Human Body Model; JESD22-A114	CLASS 1C		
	Machine Model; JESD22-A115	CLASS B		

### Notes:

5. Repetitive rating: Pulse width limited by maximum junction temperature.
6.  $L=51\text{mH}$ , starting  $T_J=25^{\circ}\text{C}$ .

## Thermal Impedance

Symbol	Parameter	Value	Unit
8-DIP <sup>(7)</sup>			
$\theta_{JA}$	Junction-to-Ambient Thermal Resistance <sup>(8)</sup>	80	$^{\circ}\text{C/W}$
$\theta_{JC}$	Junction-to-Case Thermal Resistance <sup>(9)</sup>	20	
$\theta_{JT}$	Junction-to-Top Thermal Resistance <sup>(10)</sup>	35	

### Notes:

7. All items are tested with the standards JESD 51-2 and 51-10 (DIP).
8. Free-standing with no heat-sink, under natural convection.
9. Infinite cooling condition - refer to the SEMI G30-88.
10. Measured on the package top surface.

## Electrical Characteristics

T<sub>A</sub>=25°C unless otherwise specified.

Symbol	Parameter	Condition	Min.	Typ.	Max.	Unit
<b>SenseFET Section</b>						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>CC</sub> =0V, I <sub>D</sub> =100μA	650			V
I <sub>DSS</sub>	Zero-Gate-Voltage Drain Current	V <sub>DS</sub> =650V			100	μA
R <sub>DS(ON)</sub>	Drain-Source On-State Resistance <sup>(11)</sup>	T <sub>J</sub> =25°C, I <sub>D</sub> =0.5A	FSQ0365	3.5	4.5	Ω
			FSQ0265	5.0	6.0	
			FSQ0165	8.0	10.0	
			FSQ321	14.0	19.0	
C <sub>ISS</sub>	Input Capacitance	V <sub>GS</sub> =0V, V <sub>DS</sub> =25V, f=1MHz	FSQ0365	315		pF
			FSQ0265	550		
			FSQ0165	250		
			FSQ321	162		
C <sub>OSS</sub>	Output Capacitance	V <sub>GS</sub> =0V, V <sub>DS</sub> =25V, f=1MHz	FSQ0365	47		pF
			FSQ0265	38		
			FSQ0165	25		
			FSQ321	18		
C <sub>RSS</sub>	Reverse Transfer Capacitance	V <sub>GS</sub> =0V, V <sub>DS</sub> =25V, f=1MHz	FSQ0365	9.0		pF
			FSQ0265	17.0		
			FSQ0165	10.0		
			FSQ321	3.8		
t <sub>d(on)</sub>	Turn-On Delay	V <sub>DD</sub> =350V, I <sub>D</sub> =25mA	FSQ0365	11.2		ns
			FSQ0265	20.0		
			FSQ0165	12.0		
			FSQ321	9.5		
t <sub>r</sub>	Rise Time	V <sub>DD</sub> =350V, I <sub>D</sub> =25mA	FSQ0365	34		ns
			FSQ0265	15		
			FSQ0165	4		
			FSQ321	19		
t <sub>d(off)</sub>	Turn-Off Delay	V <sub>DD</sub> =350V, I <sub>D</sub> =25mA	FSQ0365	28.2		ns
			FSQ0265	55.0		
			FSQ0165	30.0		
			FSQ321	33.0		
t <sub>f</sub>	Fall Time	V <sub>DD</sub> =350V, I <sub>D</sub> =25mA	FSQ0365	32		ns
			FSQ0265	25		
			FSQ0165	10		
			FSQ321	42		
<b>Burst-Mode Section</b>						
V <sub>BURH</sub>	Burst-Mode Voltage	T <sub>J</sub> =25°C, t <sub>PD</sub> =200ns <sup>(12)</sup>	0.45	0.55	0.65	V
V <sub>BURL</sub>			0.25	0.35	0.45	V
V <sub>BUR(HYS)</sub>				200		mV

Continued on the following page...

**Electrical Characteristics** (Continued)

 $T_A=25^\circ\text{C}$  unless otherwise specified.

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
<b>Control Section</b>						
$t_{ON,MAX1}$	Maximum On Time1	All but FSQ321 $T_J=25^\circ\text{C}$	10.5	12.0	13.5	$\mu\text{s}$
$t_{ON,MAX2}$	Maximum On Time2	FSQ321 $T_J=25^\circ\text{C}$	6.35	7.06	7.77	$\mu\text{s}$
$t_{B1}$	Blanking Time1	All but FSQ321	13.2	15.0	16.8	$\mu\text{s}$
$t_{B2}$	Blanking Time2	FSQ321	7.5	8.2		$\mu\text{s}$
$t_W$	Detection Time Window	$T_J=25^\circ\text{C}$ , $V_{sync}=0\text{V}$		3.0		$\mu\text{s}$
$\Delta f_S$	Switching Frequency Variation <sup>(14)</sup>	$-25^\circ\text{C} < T_J < 85^\circ\text{C}$		$\pm 5$	$\pm 10$	%
$I_{FB}$	Feedback Source Current	$V_{FB}=0\text{V}$	700	900	1100	$\mu\text{A}$
$D_{MIN}$	Minimum Duty Cycle	$V_{FB}=0\text{V}$			0	%
$V_{START}$	UVLO Threshold Voltage	After Turn-on	11	12	13	V
$V_{STOP}$			7	8	9	V
$t_{S/S1}$	Internal Soft-Start Time 1	All but FSQ321 With Free-Running Frequency		15		ms
$t_{S/S2}$	Internal Soft-Start Time 2	FSQ321 With Free-Running Frequency		10		ms
<b>Protection Section</b>						
$I_{LIM}$	Peak Current Limit	FSQ0365 $T_J=25^\circ\text{C}$ , $di/dt=240\text{mA}/\mu\text{s}$	1.32	1.50	1.68	A
		FSQ0265 $T_J=25^\circ\text{C}$ , $di/dt=200\text{mA}/\mu\text{s}$	1.06	1.20	1.34	
		FSQ0165 $T_J=25^\circ\text{C}$ , $di/dt=175\text{mA}/\mu\text{s}$	0.8	0.9	1.0	
		FSQ321 $T_J=25^\circ\text{C}$ , $di/dt=125\text{mA}/\mu\text{s}$	0.53	0.60	0.67	
$V_{SD}$	Shutdown Feedback Voltage	$V_{CC}=15\text{V}$	5.5	6.0	6.5	V
$I_{DELAY}$	Shutdown Delay Current	$V_{FB}=5\text{V}$	4.0	5.0	6.0	$\mu\text{A}$
$t_{LEB}$	Leading-Edge Blanking Time <sup>(13)</sup>			200		ns
$V_{OVP}$	Over-Voltage Protection	$V_{CC}=15\text{V}$ , $V_{FB}=2\text{V}$	5.5	6.0	6.5	V
$t_{OVP}$	Over-Voltage Protection Blanking Time		2	3	4	$\mu\text{s}$
$T_{SD}$	Thermal Shutdown Temperature <sup>(13)</sup>		125	140	155	$^\circ\text{C}$
<b>Sync Section</b>						
$V_{SH}$	Sync Threshold Voltage		0.55	0.70	0.85	V
$V_{SL}$			0.14	0.20	0.26	V
$t_{Sync}$	Sync Delay Time <sup>(13,14)</sup>			300		ns
<b>Total Device Section</b>						
$I_{OP}$	Operating Supply Current (Control Part Only)	$V_{CC}=15\text{V}$	1	3	5	mA
$I_{START}$	Start Current	$V_{CC}=V_{START} - 0.1\text{V}$ (Before $V_{CC}$ Reaches $V_{START}$ )	270	360	450	$\mu\text{A}$
$I_{CH}$	Startup Charging Current	$V_{CC}=0\text{V}$ , $V_{STR}=\text{Minimum } 40\text{V}$	0.65	0.85	1.00	mA
$V_{STR}$	Minimum $V_{STR}$ Supply Voltage			26		V

**Notes:**

11. Pulse test: Pulse-Width=300 $\mu\text{s}$ , duty=2%.
12. Propagation delay in the control IC.
13. Though guaranteed, it is not 100% tested in production.
14. Includes gate turn-on time.



### Comparison Between FSDM0x65RNB and FSQ-Series

Function	FSDM0x65RNB	FSQ-Series	Advantages of FSQ-Series
Operation Method	Constant Frequency PWM	Valley Switching Operation	<ul style="list-style-type: none"> <li>▪ Improved efficiency by valley switching</li> <li>▪ Reduced EMI noise</li> </ul>
EMI Reduction	Frequency Modulation	Valley Switching & Inherent Frequency Modulation	<ul style="list-style-type: none"> <li>▪ Reduce EMI noise in two ways</li> </ul>
Burst-Mode Operation	Fixed Burst Peak	Advanced Burst-Mode	<ul style="list-style-type: none"> <li>▪ Improved standby power by valley switching also in burst-mode</li> <li>▪ Because the current peak during burst operation is dependent on <math>V_{FB}</math>, it is easier to solve audible noise</li> </ul>
Protection		AOCP	<ul style="list-style-type: none"> <li>▪ Improved reliability through precise abnormal over-current protection</li> </ul>

## Typical Performance Characteristics

Characteristic graphs are normalized at  $T_A=25^\circ\text{C}$ .

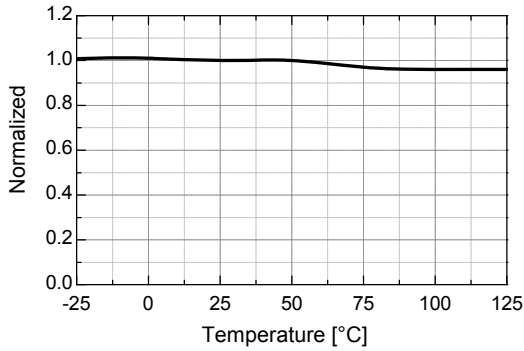


Figure 4. Operating Supply Current ( $I_{OP}$ ) vs.  $T_A$

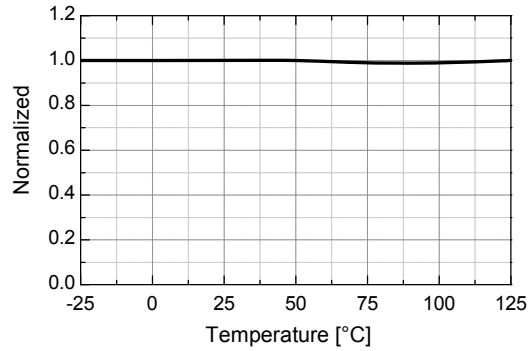


Figure 5. UVLO Start Threshold Voltage ( $V_{START}$ ) vs.  $T_A$

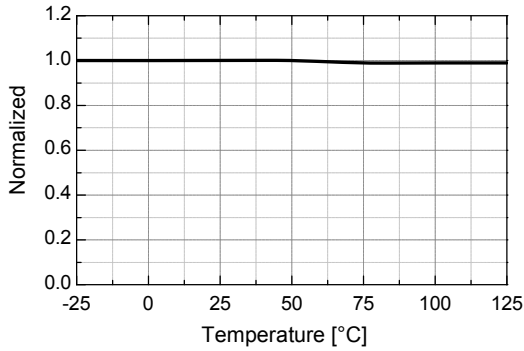


Figure 6. UVLO Stop Threshold Voltage ( $V_{STOP}$ ) vs.  $T_A$

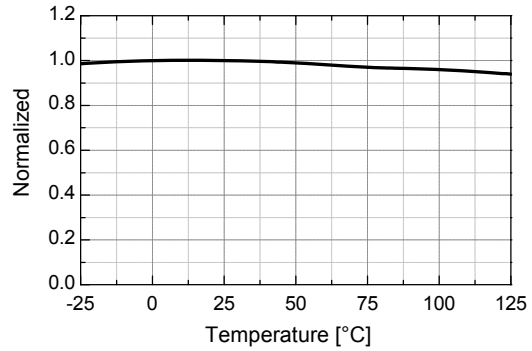


Figure 7. Startup Charging Current ( $I_{CH}$ ) vs.  $T_A$

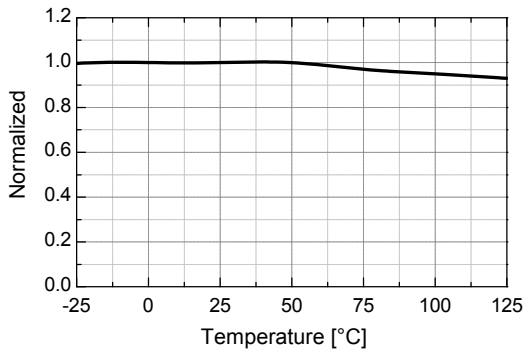


Figure 8. Initial Switching Frequency ( $f_S$ ) vs.  $T_A$

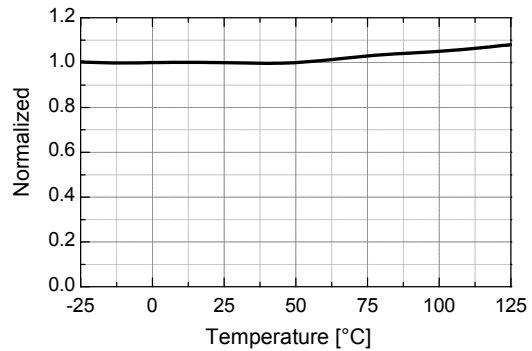


Figure 9. Maximum On Time ( $t_{ON,MAX}$ ) vs.  $T_A$

## Typical Performance Characteristics (Continued)

Characteristic graphs are normalized at  $T_A=25^\circ\text{C}$ .

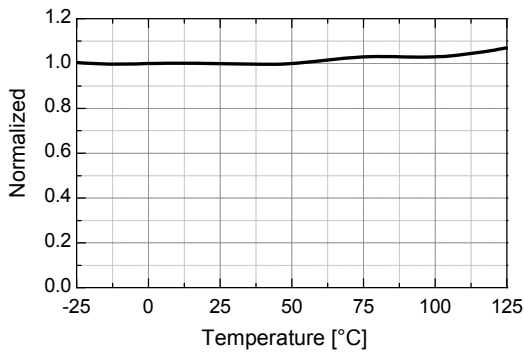


Figure 10. Blanking Time ( $t_B$ ) vs.  $T_A$

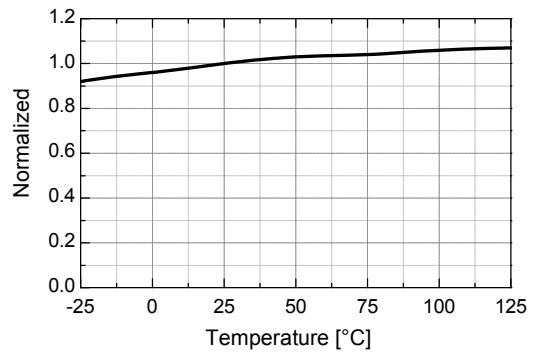


Figure 11. Feedback Source Current ( $I_{FB}$ ) vs.  $T_A$

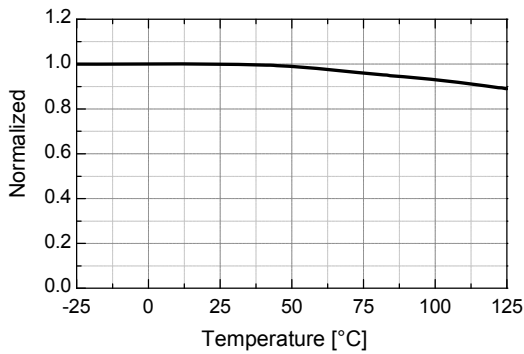


Figure 12. Shutdown Delay Current ( $I_{DELAY}$ ) vs.  $T_A$

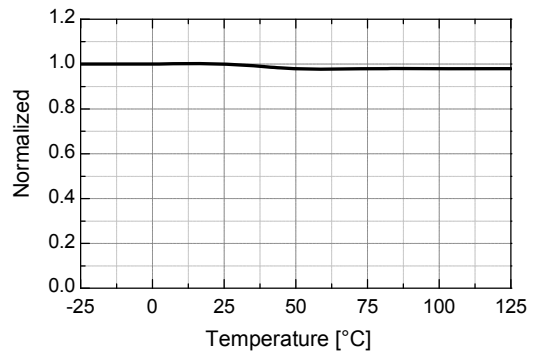


Figure 13. Burst Mode High Threshold Voltage ( $V_{burh}$ ) vs.  $T_A$

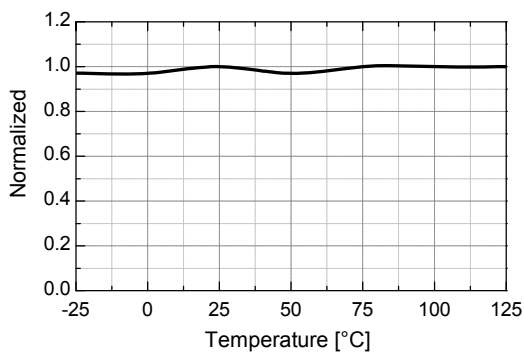


Figure 14. Burst Mode Low Threshold Voltage ( $V_{burl}$ ) vs.  $T_A$

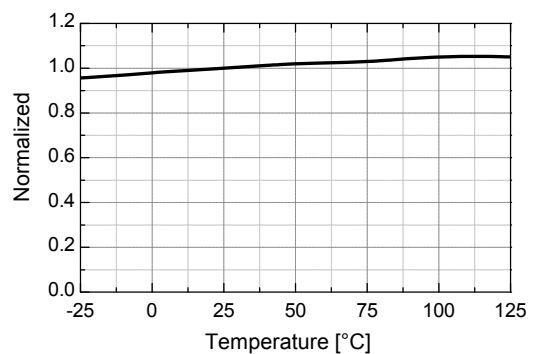


Figure 15. Peak Current Limit ( $I_{LIM}$ ) vs.  $T_A$

## Typical Performance Characteristics (Continued)

Characteristic graphs are normalized at  $T_A=25^\circ\text{C}$ .

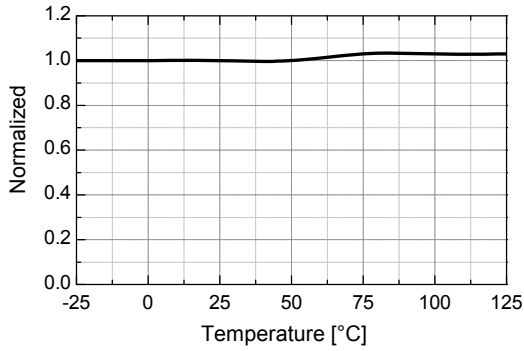


Figure 16. Sync High Threshold ( $V_{SH}$ ) vs.  $T_A$

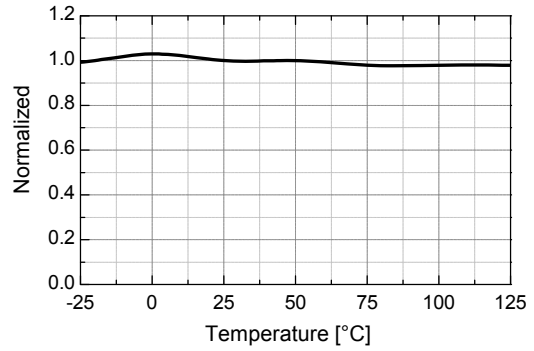


Figure 17. Sync Low Threshold Voltage ( $V_{SL}$ ) vs.  $T_A$

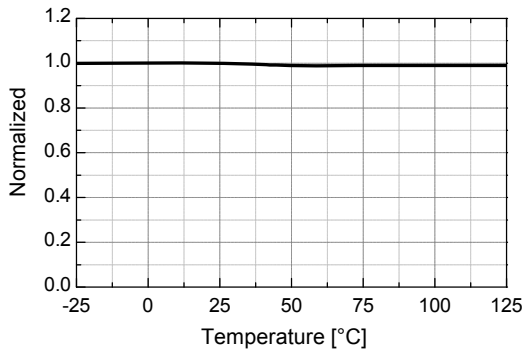


Figure 18. Shutdown Feedback Voltage ( $V_{SD}$ ) vs.  $T_A$

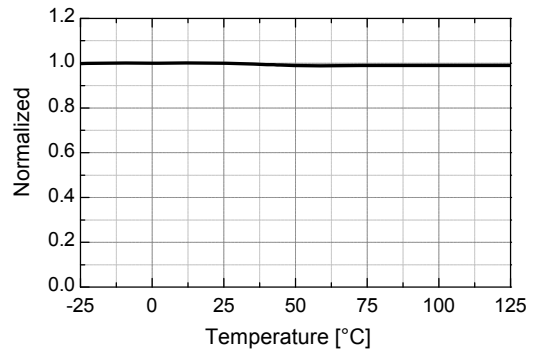


Figure 19. Over-Voltage Protection ( $V_{OP}$ ) vs.  $T_A$



the auto-restart can alternately enable and disable the switching of the power SenseFET until the fault condition is eliminated. Because these protection circuits are fully integrated into the IC without external components, the reliability is improved without increasing cost.

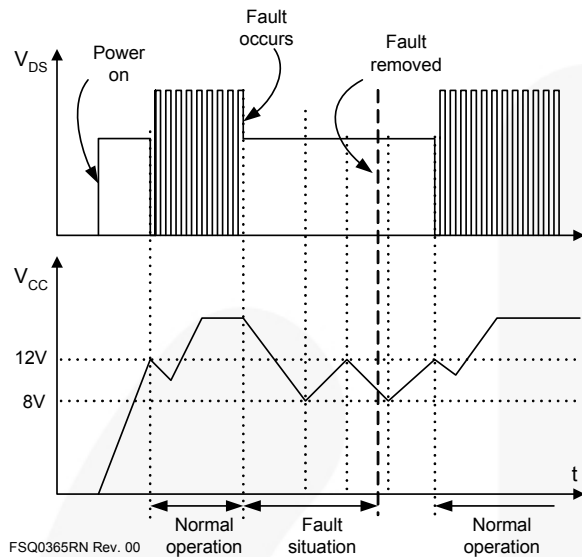


Figure 23. Auto-Restart Protection Waveforms

**4.1 Overload Protection (OLP):** Overload is defined as the load current exceeding its normal level due to an unexpected abnormal event. In this situation, the protection circuit should trigger to protect the SMPS. However, even when the SMPS is in the normal operation, the overload protection circuit can be triggered during load transition. To avoid this undesired operation, the overload protection circuit is designed to trigger only after a specified time to determine whether it is a transient situation or a true overload situation. Because of the pulse-by-pulse current limit capability, the maximum peak current through the SenseFET is limited, and therefore the maximum input power is restricted with a given input voltage. If the output consumes more than this maximum power, the output voltage ( $V_O$ ) decreases below the set voltage. This reduces the current through the opto-coupler LED, which also reduces the opto-coupler transistor current, thus increasing the feedback voltage ( $V_{FB}$ ). If  $V_{FB}$  exceeds 2.8V, D1 is blocked and the 5 $\mu$ A current source starts to charge CB slowly up to  $V_{CC}$ . In this condition,  $V_{FB}$  continues increasing until it reaches 6V, when the switching operation is terminated, as shown in Figure 24. The delay for shutdown is the time required to charge CB from 2.8V to 6V with 5 $\mu$ A. A 20 ~ 50ms delay is typical for most applications.

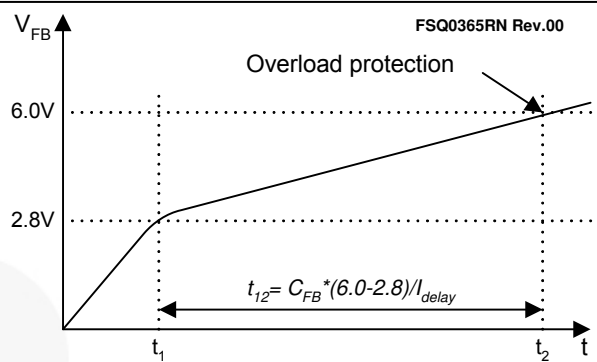


Figure 24. Overload Protection

**4.2 Abnormal Over-Current Protection (AOCP):** When the secondary rectifier diodes or the transformer pins are shorted, a steep current with extremely high-di/dt can flow through the SenseFET during the LEB time. Even though the FSQ-series has Overload Protection (OLP), it is not enough to protect the FSQ-series in that abnormal case, since severe current stress is imposed on the SenseFET until OLP triggers. The FSQ-series has an internal Abnormal Over-Current Protection (AOCP) circuit as shown in Figure 25. When the gate turn-on signal is applied to the power SenseFET, the AOCP block is enabled and monitors the current through the sensing resistor. The voltage across the resistor is compared with a preset AOCP level. If the sensing resistor voltage is greater than the AOCP level, the set signal is applied to the latch, resulting in the shutdown of the SMPS.

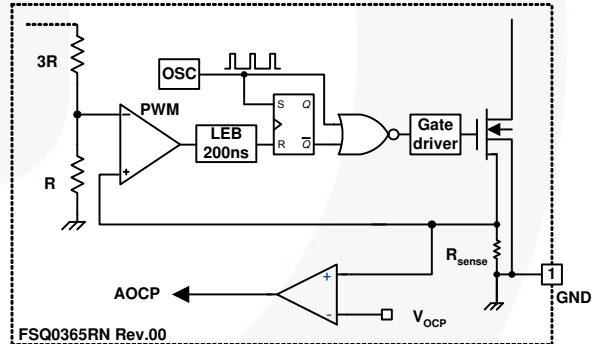


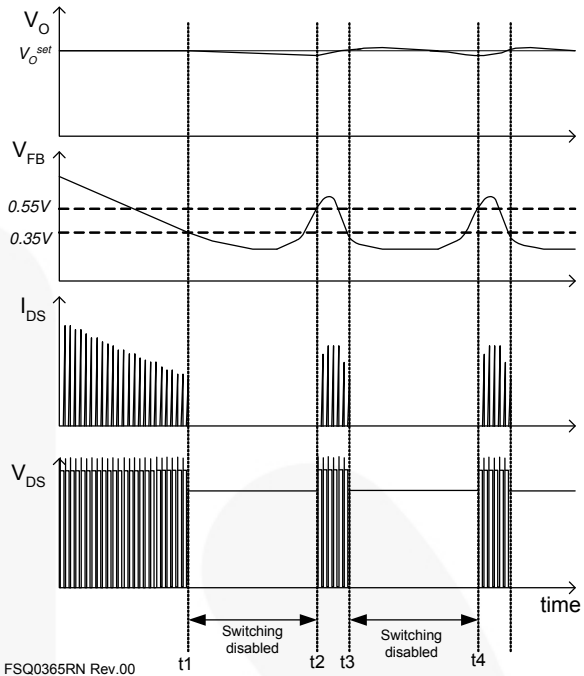
Figure 25. Abnormal Over-Current Protection

**4.3 Over-Voltage Protection (OVP):** If the secondary-side feedback circuit malfunctions or a solder defect causes an opening in the feedback path, the current through the opto-coupler transistor becomes almost zero. Then  $V_{FB}$  climbs up in a similar manner to the overload situation, forcing the preset maximum current to be supplied to the SMPS until the overload protection triggers. Because more energy than required is provided to the output, the output voltage may exceed the rated voltage before the overload protection triggers, resulting in the breakdown of the devices in the secondary side. To prevent this situation, an OVP circuit is employed. In general, the peak voltage of the sync signal is proportional to the output voltage and the FSQ-series uses a sync signal instead of directly monitoring the output voltage. If the sync signal exceeds 6V, an OVP is triggered, shutting down the SMPS. To avoid undesired triggering of OVP during normal operation, the peak voltage of the sync signal should be designed below 6V.

**4.4 Thermal Shutdown (TSD):** The SenseFET and the control IC are built in one package. This makes it easy for the control IC to detect the abnormal over temperature of the SenseFET. If the temperature exceeds  $\sim 150^{\circ}\text{C}$ , the thermal shutdown triggers.

**5. Soft-Start:** An internal soft-start circuit increases PWM comparator inverting input voltage with the SenseFET current slowly after it starts up. The typical soft-start time is 15ms. The pulsewidth to the power switching device is progressively increased to establish the correct working conditions for transformers, inductors, and capacitors. The voltage on the output capacitors is progressively increased with the intention of smoothly establishing the required output voltage. This helps prevent transformer saturation and reduces stress on the secondary diode during startup.

**6. Burst Operation:** To minimize power dissipation in Standby Mode, the FPS enters Burst-Mode operation. As the load decreases, the feedback voltage decreases. As shown in Figure 26, the device automatically enters Burst Mode when the feedback voltage drops below  $V_{BURL}$  (350mV). At this point, switching stops and the output voltages start to drop at a rate dependent on standby current load. This causes the feedback voltage to rise. Once it passes  $V_{BURH}$  (550mV), switching resumes. The feedback voltage then falls and the process repeats. Burst Mode alternately enables and disables switching of the power SenseFET, reducing switching loss in Standby Mode.



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**Figure 26. Waveforms of Burst Operation**

**7. Switching Frequency Limit:** To minimize switching loss and Electromagnetic Interference (EMI), the MOSFET turns on when the drain voltage reaches its minimum value in valley switching operation. However, this causes switching frequency to increase at light load conditions. As the load decreases, the peak drain current diminishes and the switching frequency increases. This results in severe switching losses at light-load condition, as well as intermittent switching and audible noise. Because of these problems, the valley switching converter topology has limitations in a wide range of applications.

To overcome this problem, FSQ-series employs a frequency-limit function, as shown in Figure 27 and Figure 28. Once the SenseFET is turned on, the next turn-on is prohibited during the blanking time ( $t_B$ ). After the blanking time, the controller finds the valley within the detection time window ( $t_W$ ) and turns on the MOSFET, as shown in Figure 27 and Figure 28 (cases A, B, and C). If no valley is found during  $t_W$ , the internal SenseFET is forced to turn on at the end of  $t_W$  (case D). Therefore, FSQ devices have a minimum switching frequency of 55kHz and a maximum switching frequency of 67kHz, as shown in Figure 28.

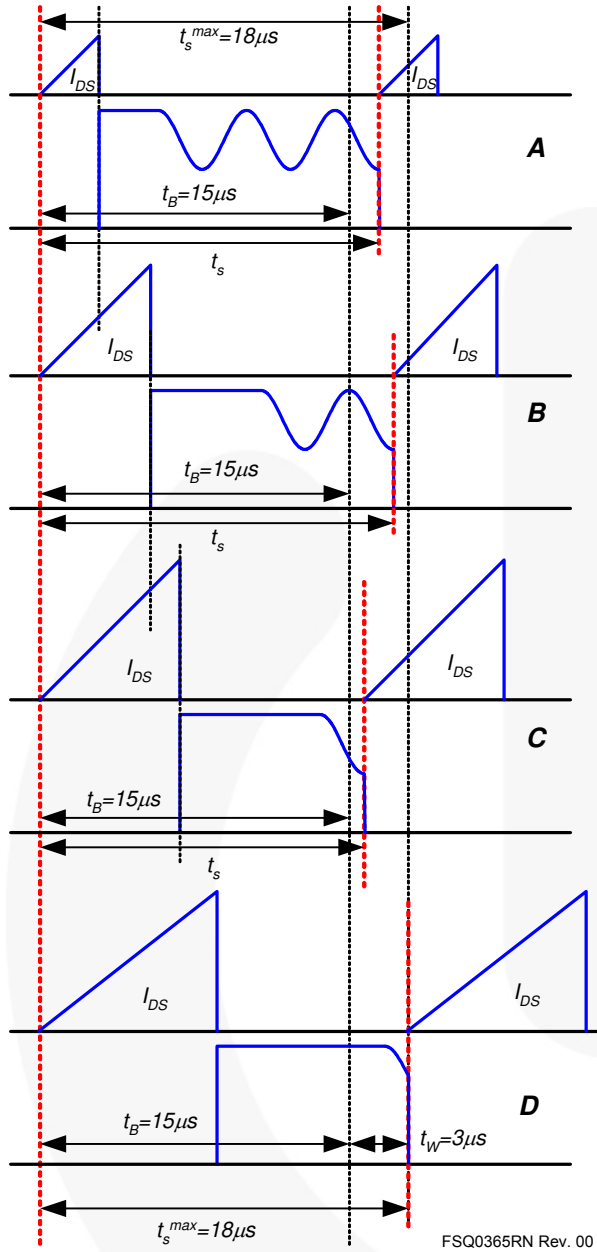
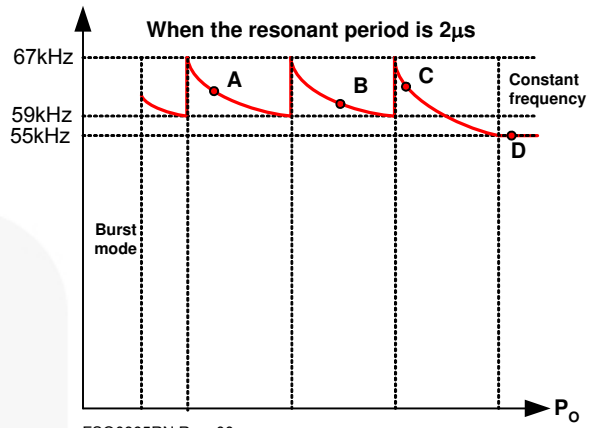


Figure 27. Valley Switching with Limited Frequency



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Figure 28. Switching Frequency Range





## Transformer

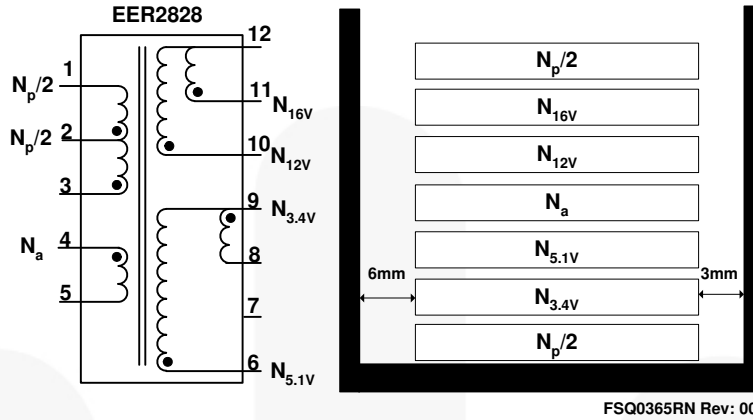


Figure 30. Transformer Schematic Diagram of FSQ0365RN

Table 1. Winding Specification

No.	Pin (s→f)	Wire	Turns	Winding Method
$N_p/2$	3→2	0.25 <sup>φ</sup> x 1	50	Center Solenoid Winding
Insulation: Polyester Tape t = 0.050mm, 2-Layer				
$N_{3.4V}$	9→8	0.33 <sup>φ</sup> x 2	4	Center Solenoid Winding
Insulation: Polyester Tape t = 0.050mm, 2-Layer				
$N_{5V}$	6→9	0.33 <sup>φ</sup> x 1	2	Center Solenoid Winding
Insulation: Polyester Tape t = 0.050mm, 2-Layer				
$N_a$	4→5	0.25 <sup>φ</sup> x 1	16	Center Solenoid Winding
Insulation: Polyester Tape t = 0.050mm, 2-Layer				
$N_{12V}$	10→12	0.33 <sup>φ</sup> x 3	14	Center Solenoid Winding
Insulation: Polyester Tape t = 0.050mm, 3-Layer				
$N_{16V}$	11→12	0.33 <sup>φ</sup> x 3	18	Center Solenoid Winding
Insulation: Polyester Tape t = 0.050mm, 2-Layer				
$N_p/2$	2→1	0.25 <sup>φ</sup> x 1	50	Center Solenoid Winding
Insulation: Polyester Tape t = 0.050mm, 2-Layer				

Table 2. Electrical Characteristics

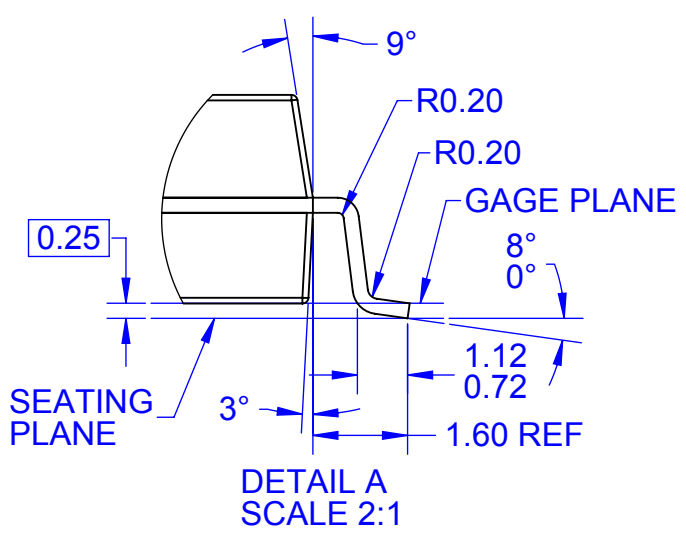
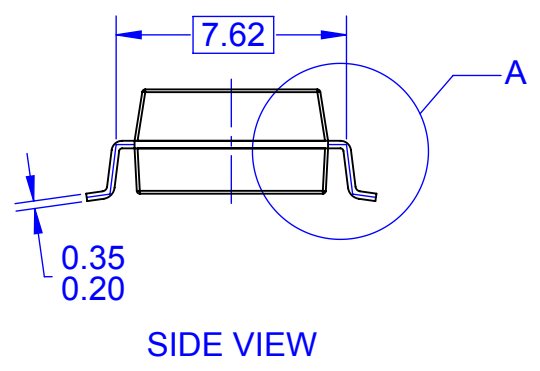
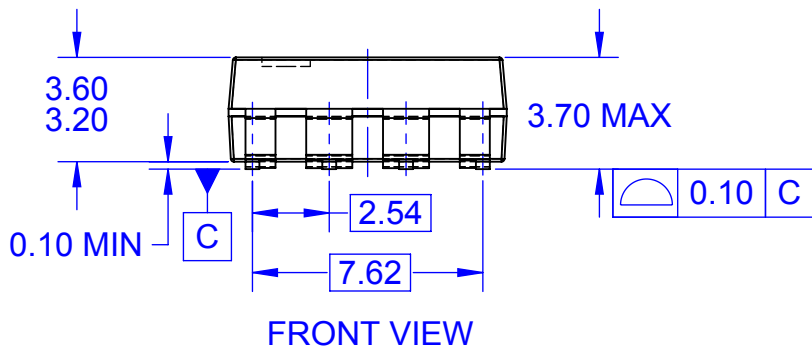
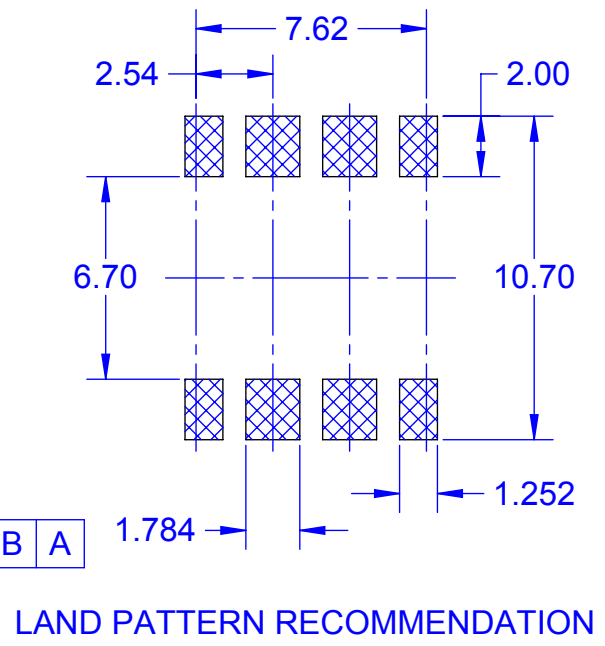
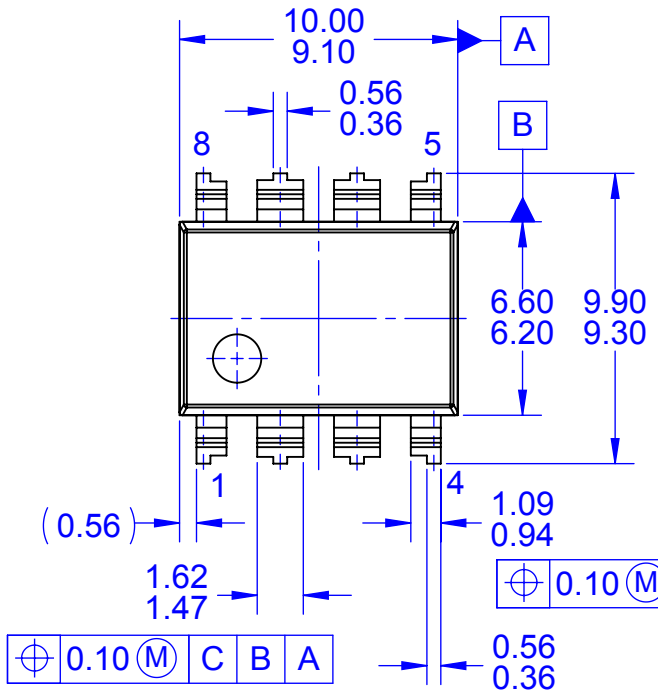
	Pin	Specification	Remarks
Inductance	1 - 3	1.4mH ± 10%	100kHz, 1V
Leakage	1 - 3	25μH Maximum	Short All Other Pins

### Core & Bobbin

- Core: EER2828 ( $A_e=86.66\text{mm}^2$ )
- Bobbin: EER2828

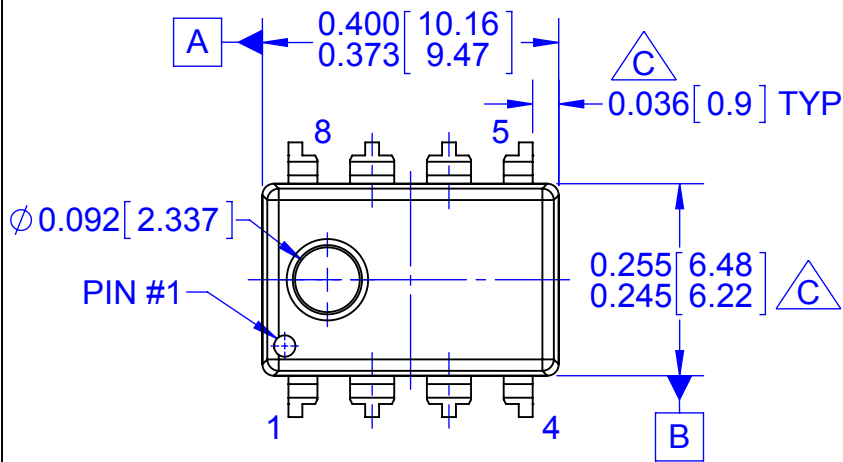
**Table 3. Demo Board Part List**

Part	Value	Note	Part	Value	Note
<b>Resistor</b>			<b>Inductor</b>		
R102	56k	1W	L201	10μH	
R103	5	1/2W	L202	10μH	
R104	12k	1/4W	L203	4.9μH	
R105	100k	1/4W	L204	4.9μH	
R106	6.2k	1/4W	<b>Diode</b>		
R107	6.2k	1/4W	D101	IN4007	
R108	62	1W	D102	IN4004	
R201	510	1/4W	ZD101	1N4746A	
R202	1k	1/4W	D103	1N4148	
R203	6.2k	1/4W	D201	UF4003	
R204	20k	1/4W	D202	UF4003	
R205	6k	1/4W	D203	SB360	
<b>Capacitor</b>			D204	SB360	
C101	100nF/275V <sub>AC</sub>	Box Capacitor	<b>IC</b>		
C102	100nF/275V <sub>AC</sub>	Box Capacitor	IC101	FSQ0365RN	FPS™
C103	33μF/400V	Electrolytic Capacitor	IC201	KA431 (TL431)	Voltage reference
C104	10nF/630V	Film Capacitor	IC202	FOD817A	Opto-coupler
C105	47nF/50V	Mono Capacitor	<b>Fuse</b>		
C106	100nF/50V	SMD (1206)	Fuse	2A/250V	
C107	22μF/50V	Electrolytic Capacitor	<b>NTC</b>		
C110	33pF/50V	Ceramic Capacitor	RT101	5D-9	
C201	470μF/35V	Electrolytic Capacitor	<b>Bridge Diode</b>		
C202	470μF/35V	Electrolytic Capacitor	BD101	2KBP06M2N257	Bridge Diode
C203	470μF/35V	Electrolytic Capacitor	<b>Line Filter</b>		
C204	470μF/35V	Electrolytic Capacitor	LF101	40mH	
C205	1000μF/10V	Electrolytic Capacitor	<b>Transformer</b>		
C206	1000μF/10V	Electrolytic Capacitor	T101		
C207	1000μF/10V	Electrolytic Capacitor	<b>Varistor</b>		
C208	1000μF/10V	Electrolytic Capacitor	TNR	10D471K	
C209	100nF /50V	Ceramic Capacitor			

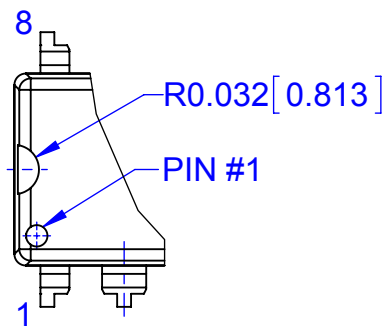


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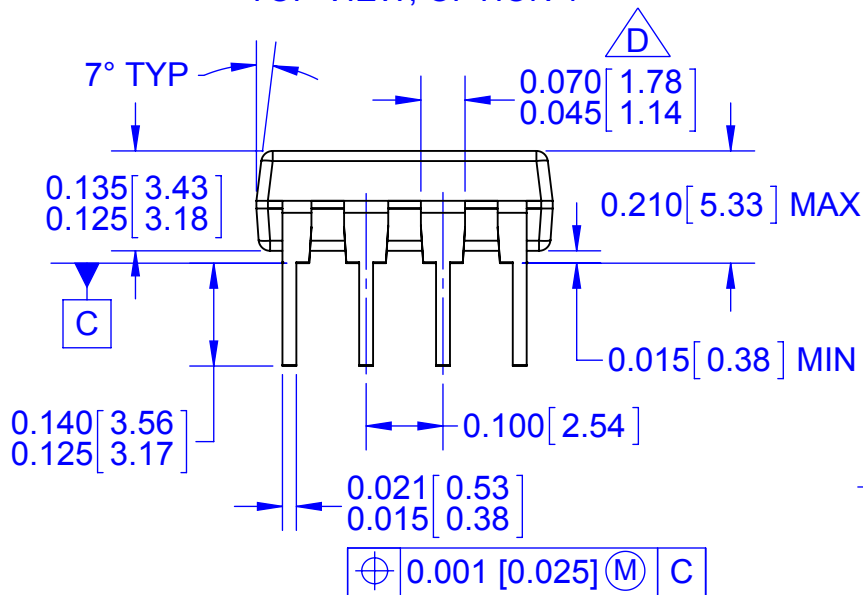




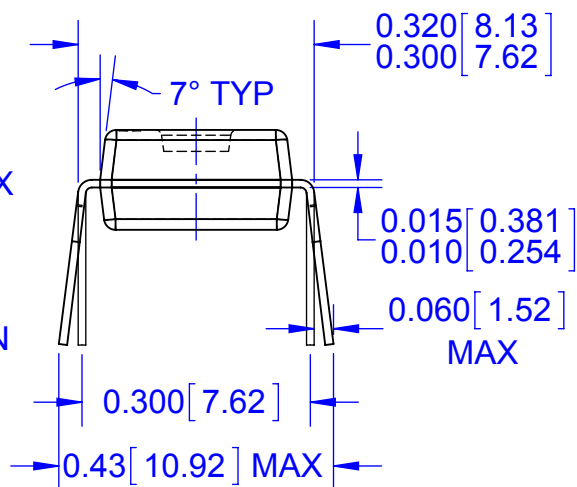
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TOP VIEW, OPTION 2



FRONT VIEW



SIDE VIEW

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